

# Beyond classical circuit design

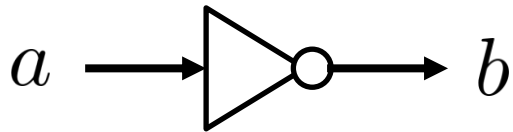
## lecture 8

### CMOS Synthesis

# Further Reading

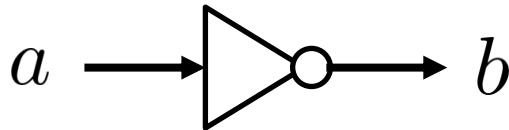
Jan M. Rabaey, Anantha Chandrakasan, Borivoje Nikolic: *Digital Integrated Circuits. A Design Perspective. 2<sup>nd</sup> edition*. Prentice Hall, 2003.

# Back to synthesis...

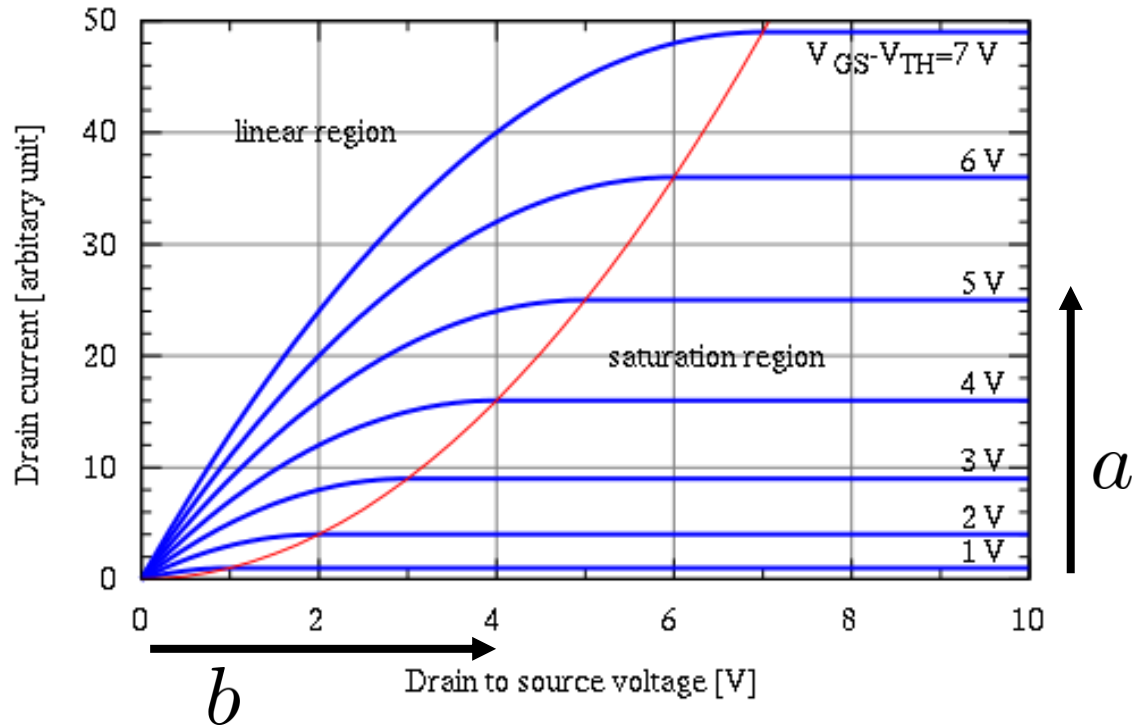
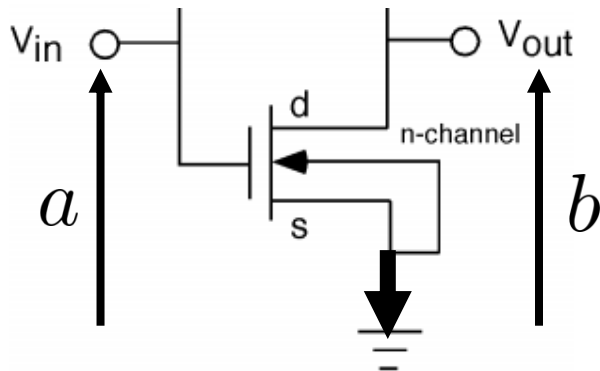


$$\begin{array}{l} a \rightarrow b \downarrow \\ \neg a \rightarrow b \uparrow \end{array}$$

# Back to synthesis...



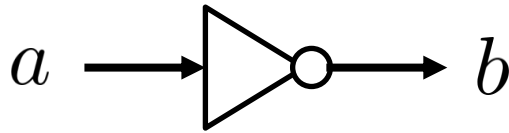
$$a \rightarrow b \downarrow$$
$$\neg a \rightarrow b \uparrow$$



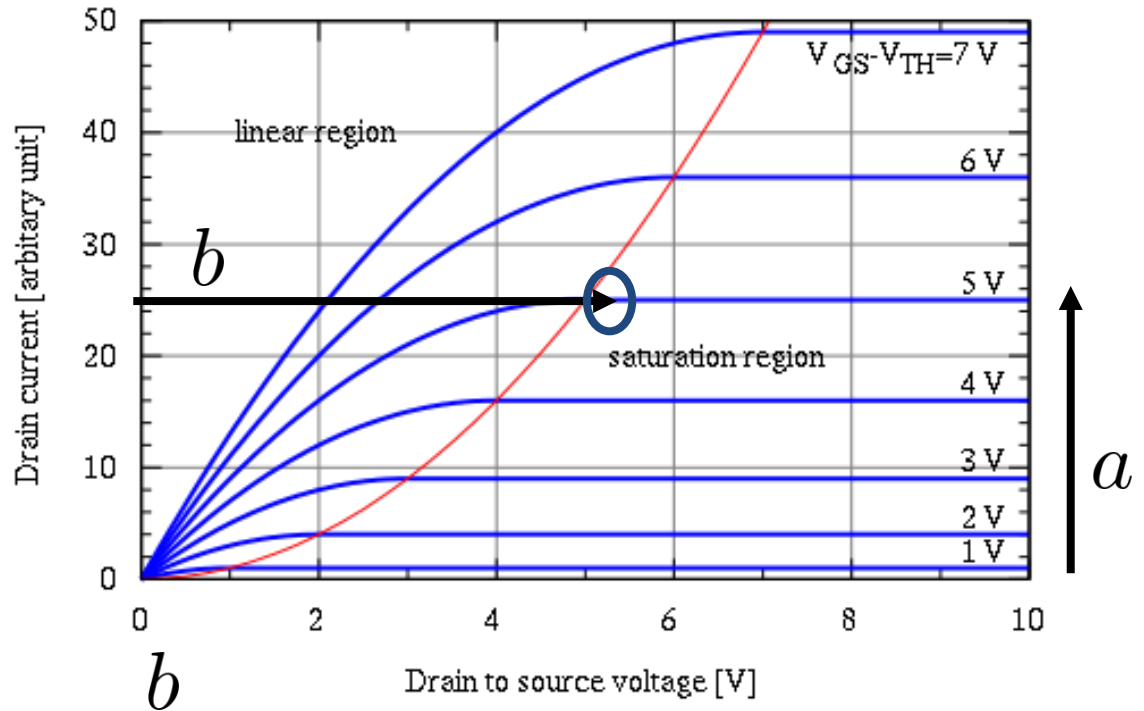
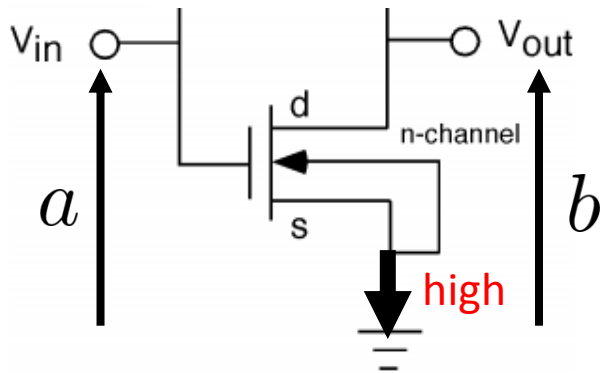
L: by Bill Wilson, [cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS\\_Logic](https://cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS_Logic)

R: [commons.wikimedia.org/wiki/File:lvsV\\_mosfet.svg#/media/File:lvsV\\_mosfet.svg](https://commons.wikimedia.org/wiki/File:lvsV_mosfet.svg#/media/File:lvsV_mosfet.svg)

# Back to synthesis...



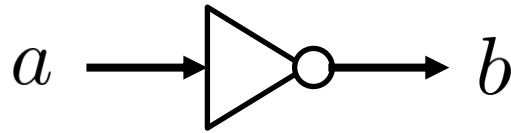
$$a \rightarrow b \downarrow$$
$$\neg a \rightarrow b \uparrow$$



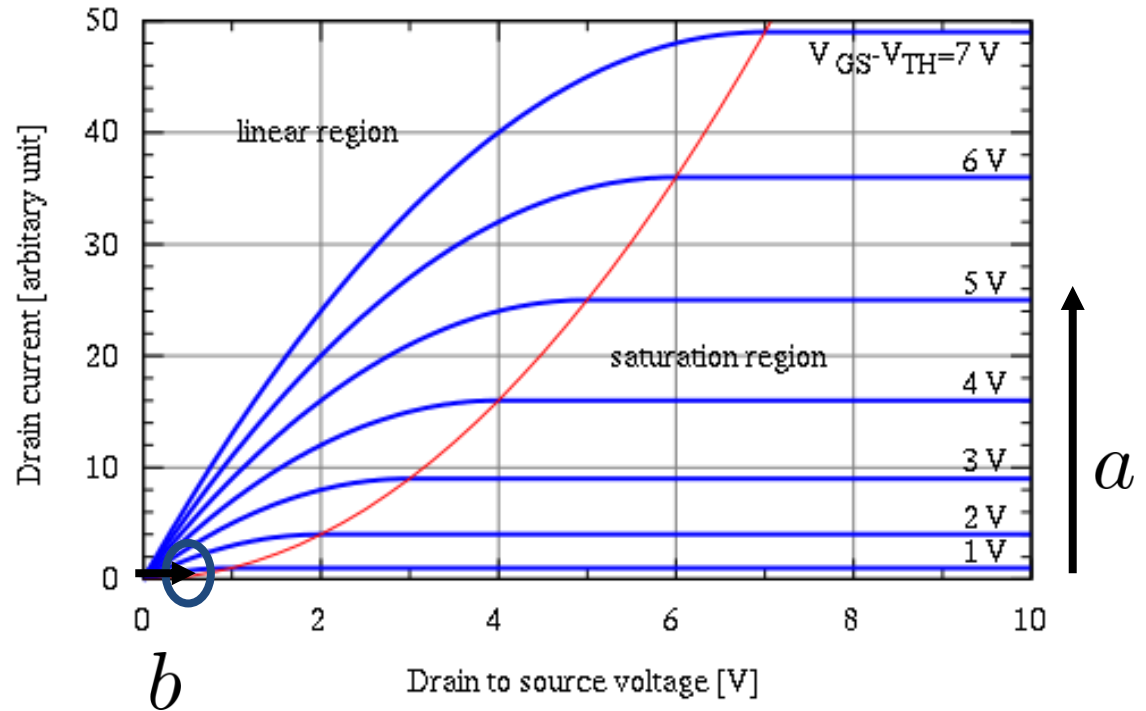
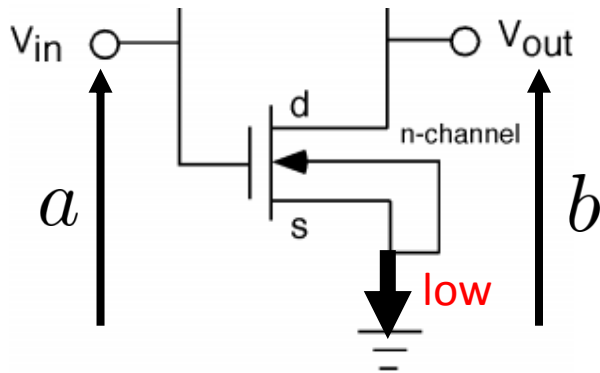
L: by Bill Wilson, [cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS\\_Logic](https://cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS_Logic)

R: [commons.wikimedia.org/wiki/File:lvsv\\_mosfet.svg#/media/File:lvsv\\_mosfet.svg](https://commons.wikimedia.org/wiki/File:lvsv_mosfet.svg#/media/File:lvsv_mosfet.svg)

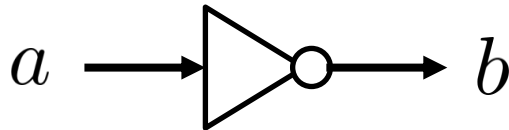
# Back to synthesis...



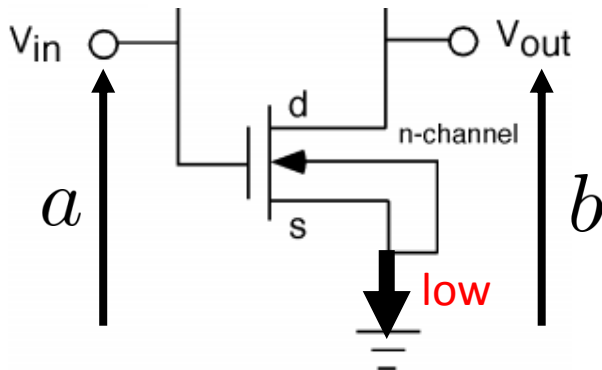
$$a \rightarrow b \downarrow$$
$$\neg a \rightarrow b \uparrow$$



# Back to synthesis...



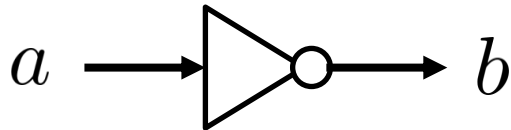
$$a \rightarrow b \downarrow$$
$$\neg a \rightarrow b \uparrow$$



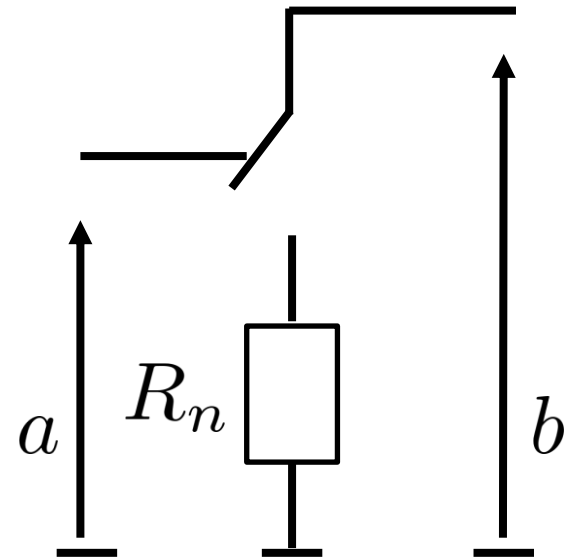
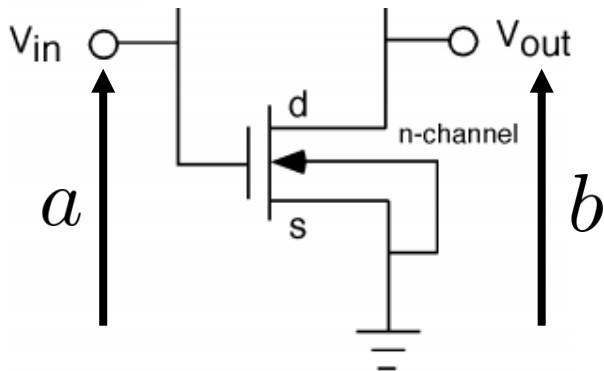
low  $a \rightarrow$   
nFET in cutoff region

high  $a \rightarrow$   
nFET in ohmic region

# Back to synthesis...

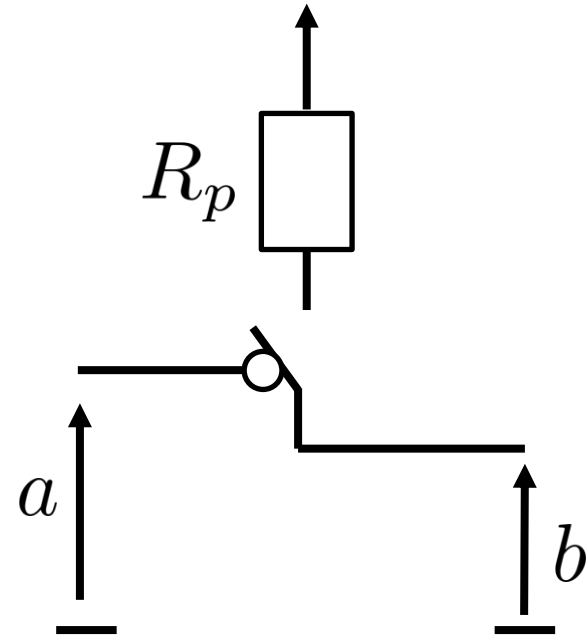
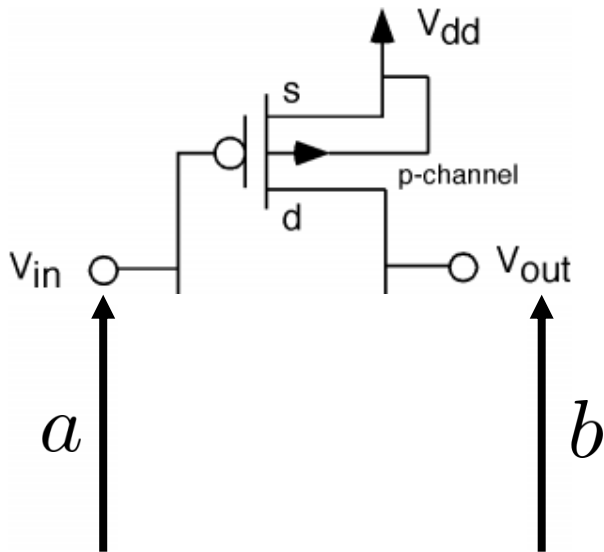
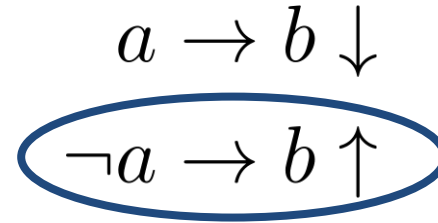
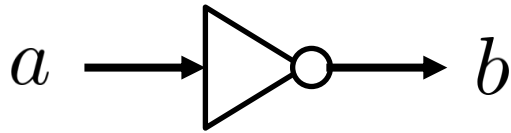


$$a \rightarrow b \downarrow$$
$$\neg a \rightarrow b \uparrow$$

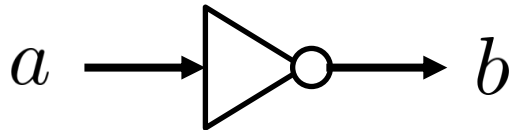




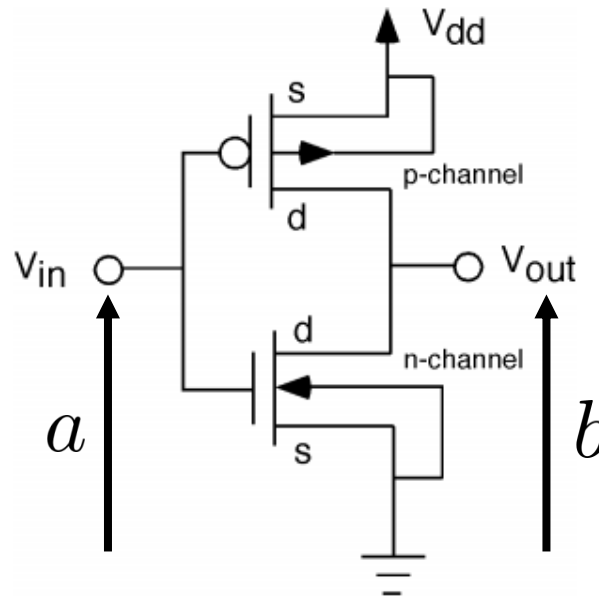
# Back to synthesis...



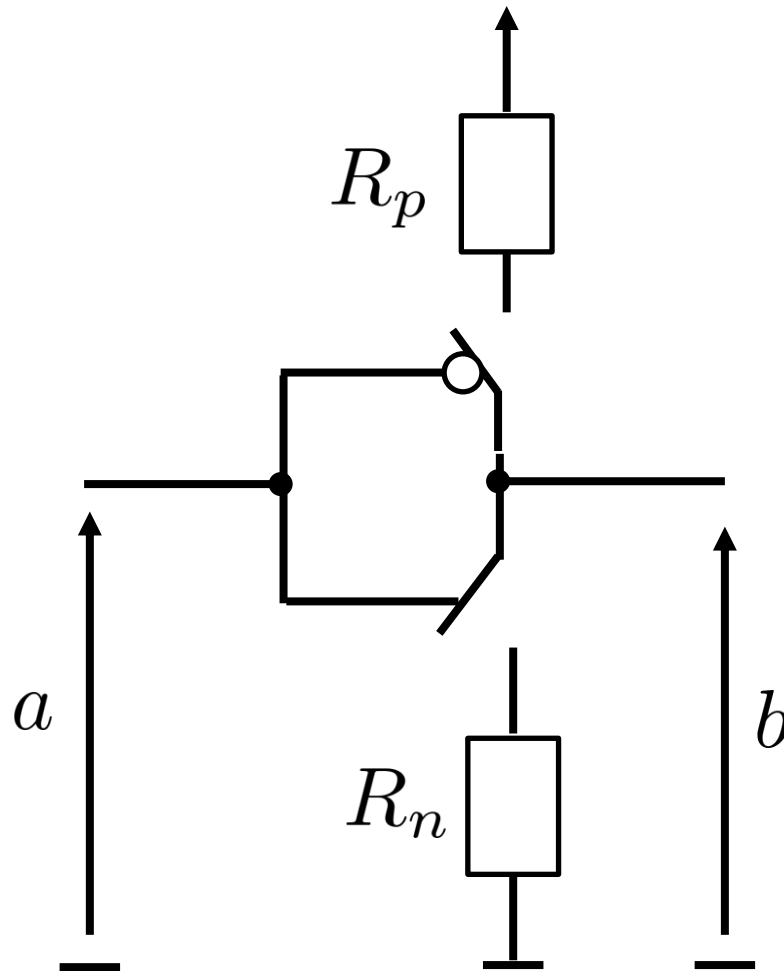
# Putting it together



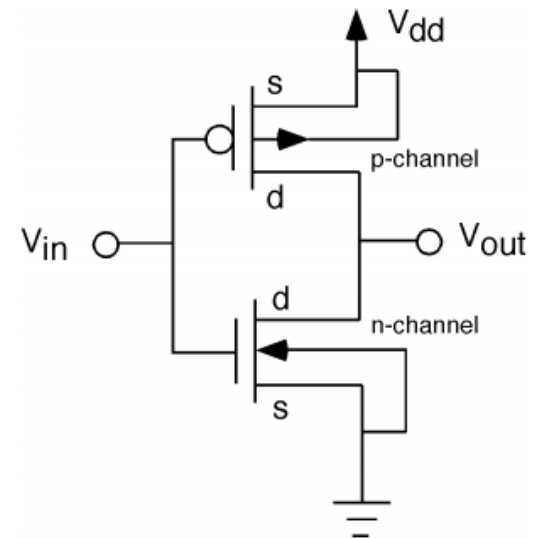
$$a \rightarrow b \downarrow$$
$$\neg a \rightarrow b \uparrow$$



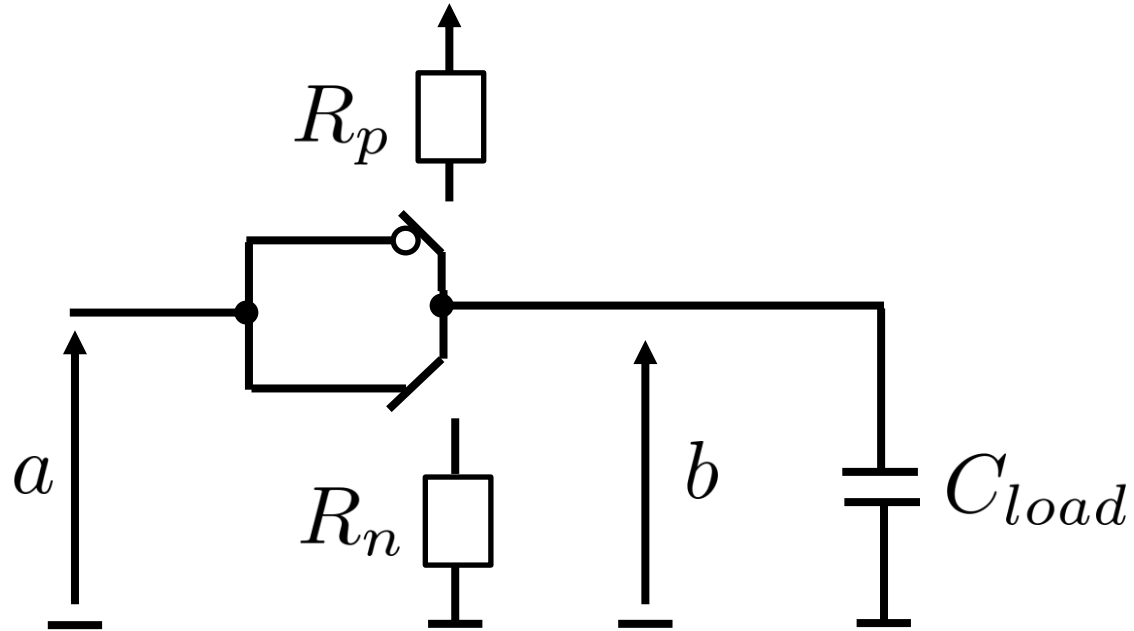
# CMOS Inverter – switch model

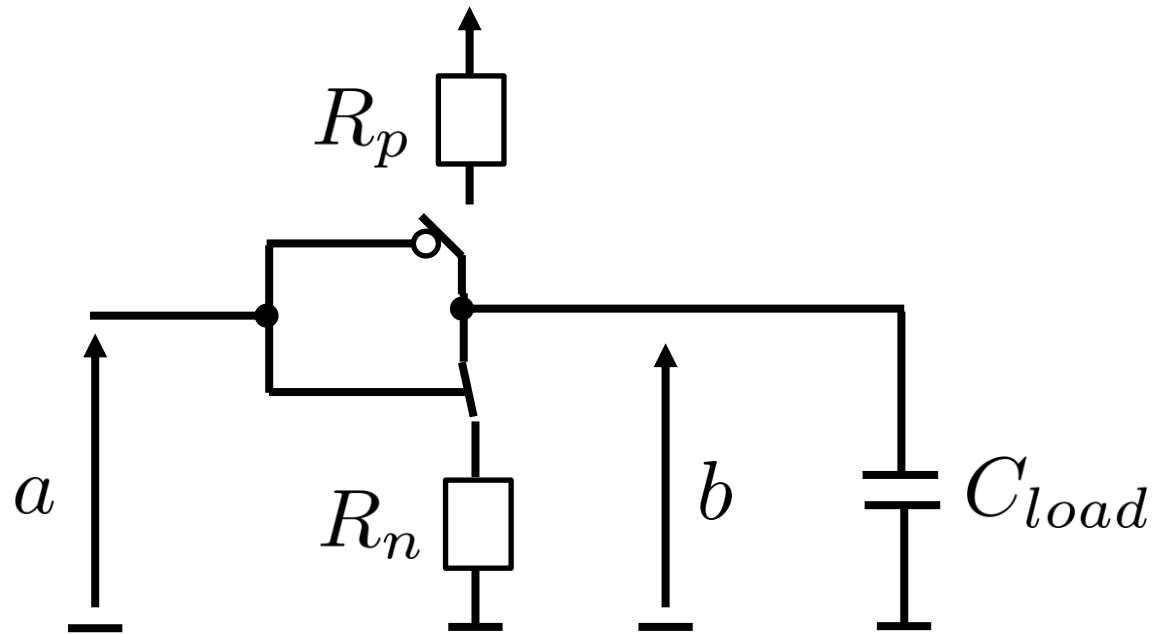


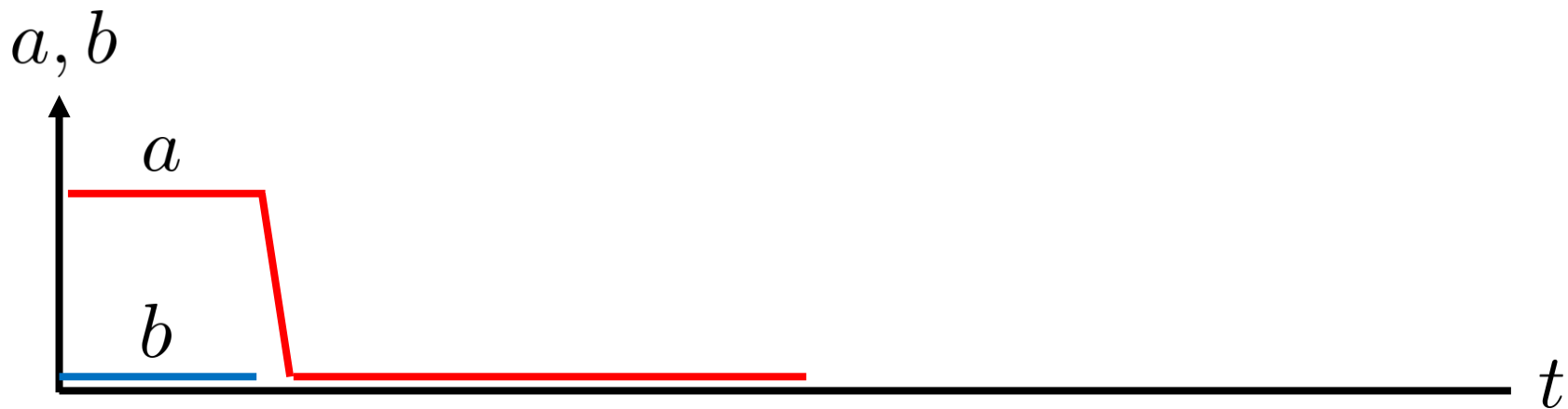
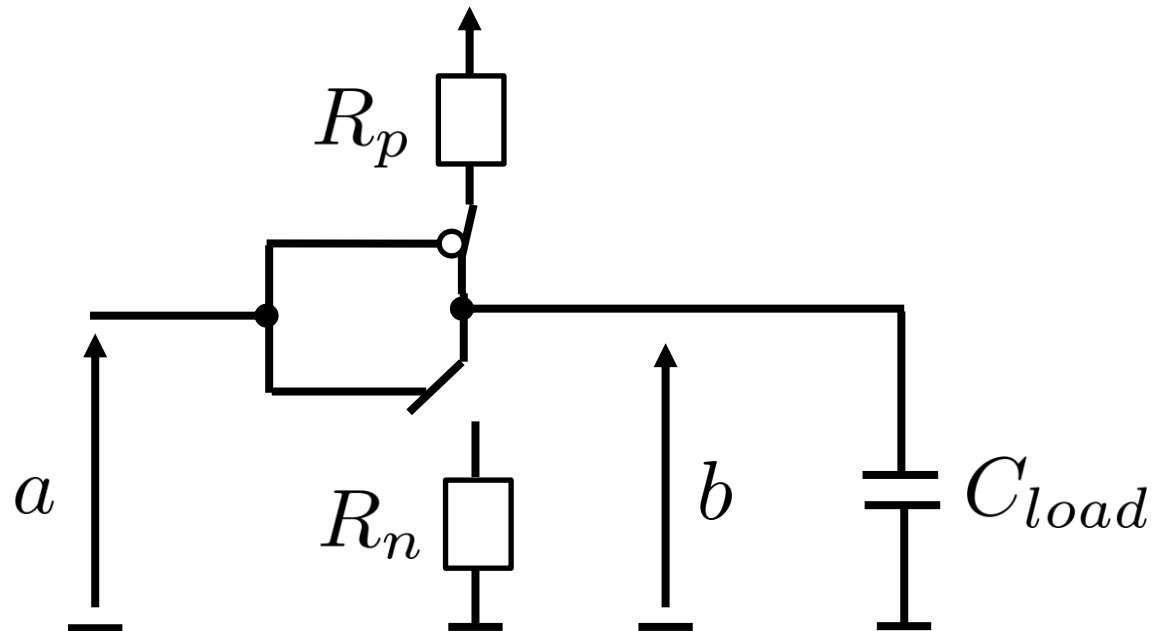
Transistor sizing  
 $R \propto L/W$

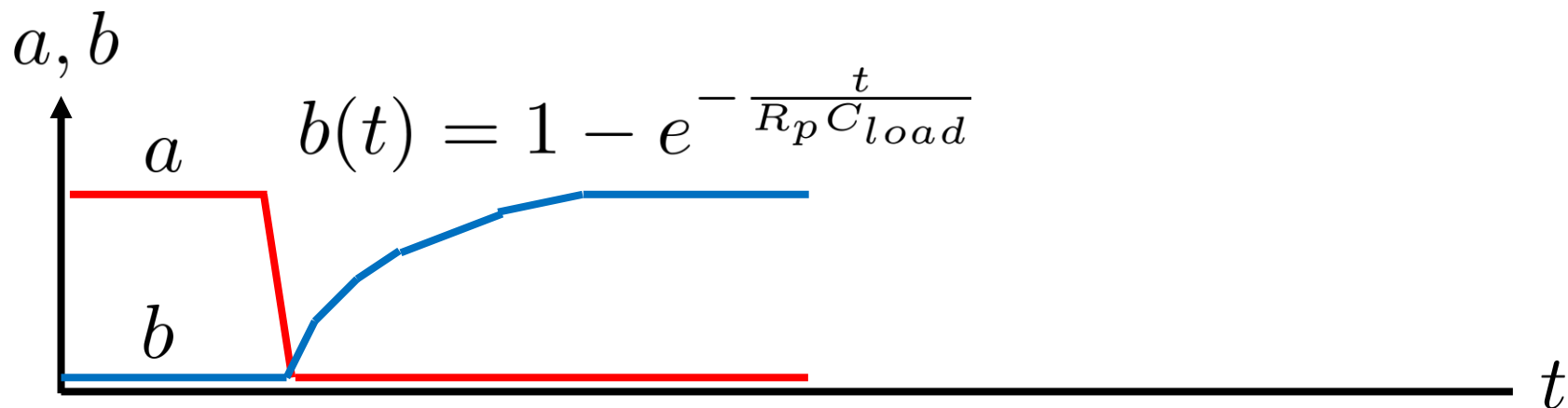
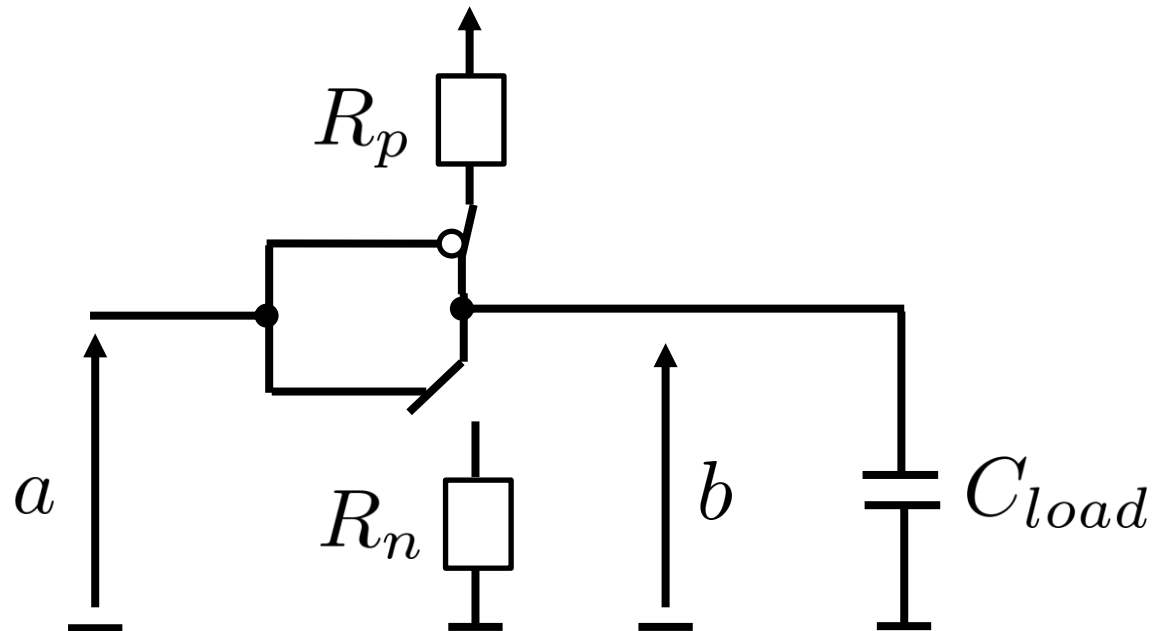


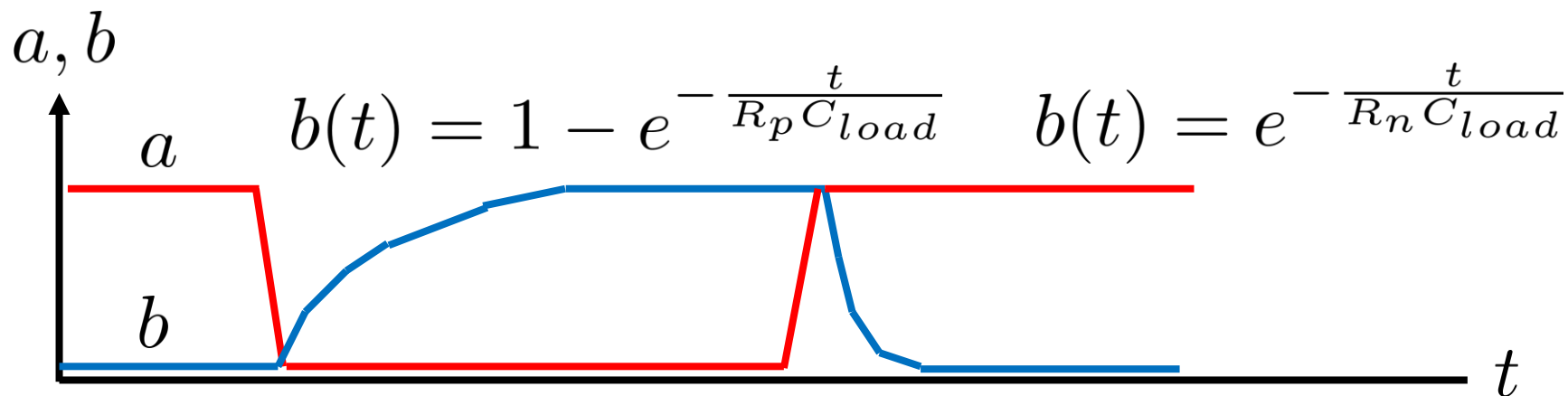
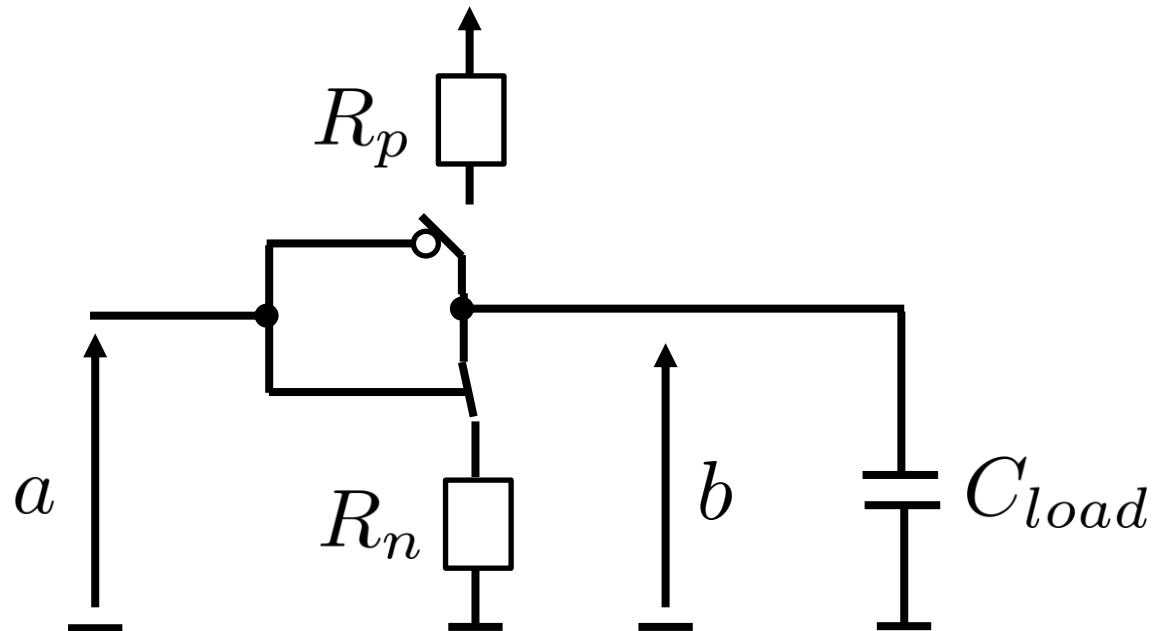
# CMOS Inverter – switch transient





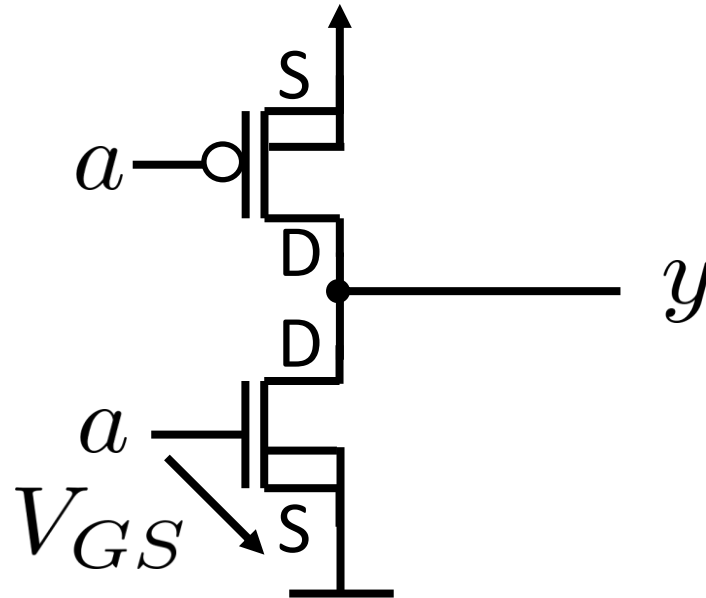








# Why this way?



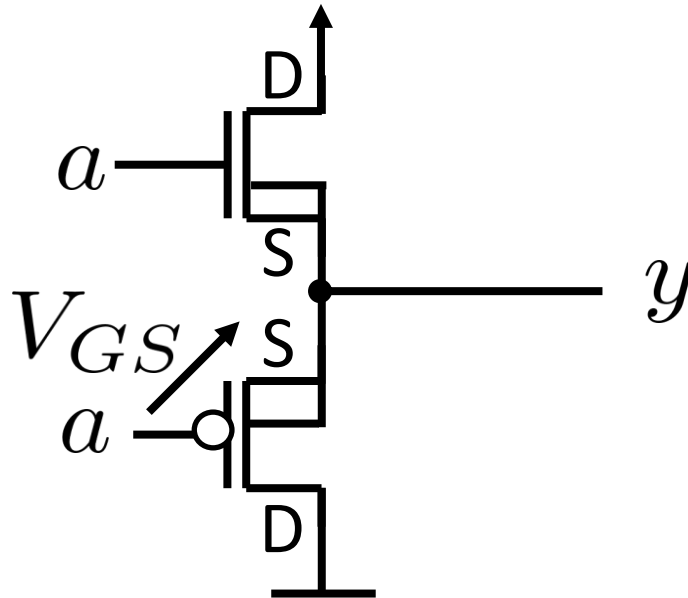
$V_{GS}$  independent of  $y$

-> high  $a$  -> nMOS always connects

-> pulls down  $y$  to 0V (= strong 0)

# pMOS pulling down

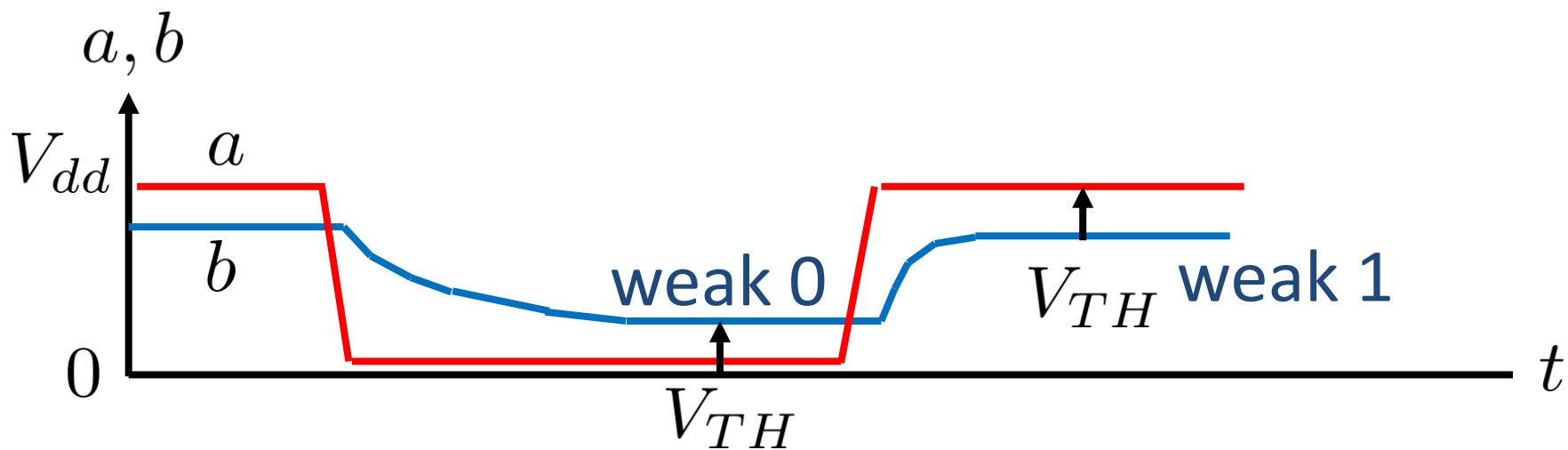
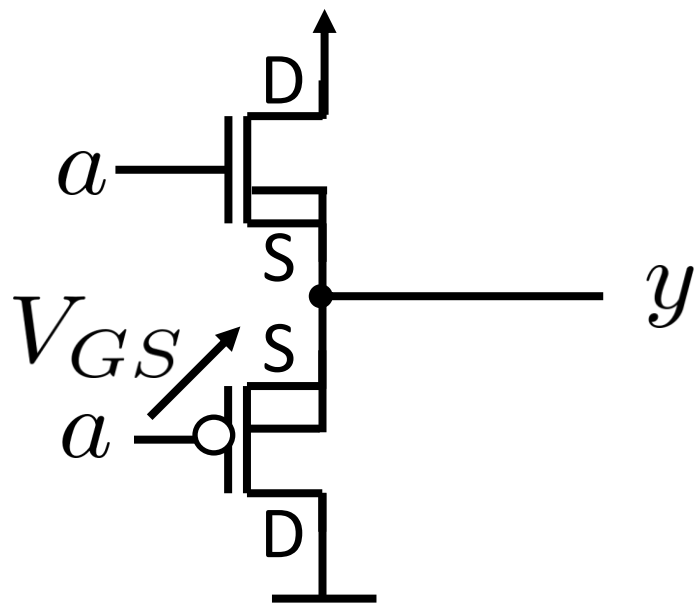
... not inverter,  
but also:



$V_{GS}$  depends on  $y$

-> when  $y \leq V_{TH}$ : pMOS cutoff

-> pulls down  $y$  to  $V_{TH}$  (= weak 0)



# CMOS

nMOS:

drives strong 0, weak 1

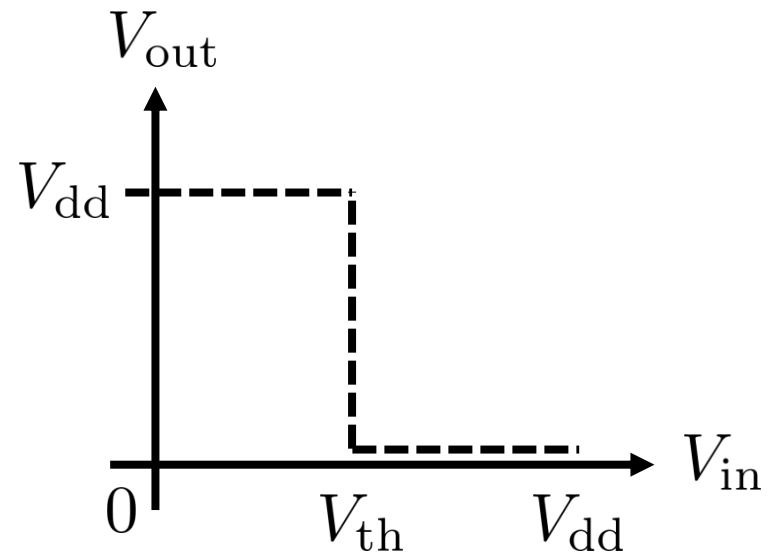
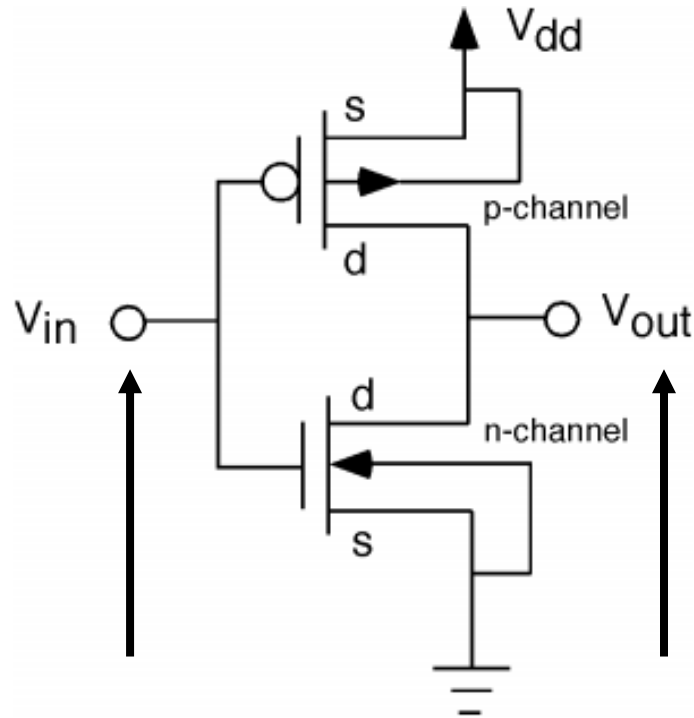
-> used for pull-down

pMOS:

drives strong 1, weak 0

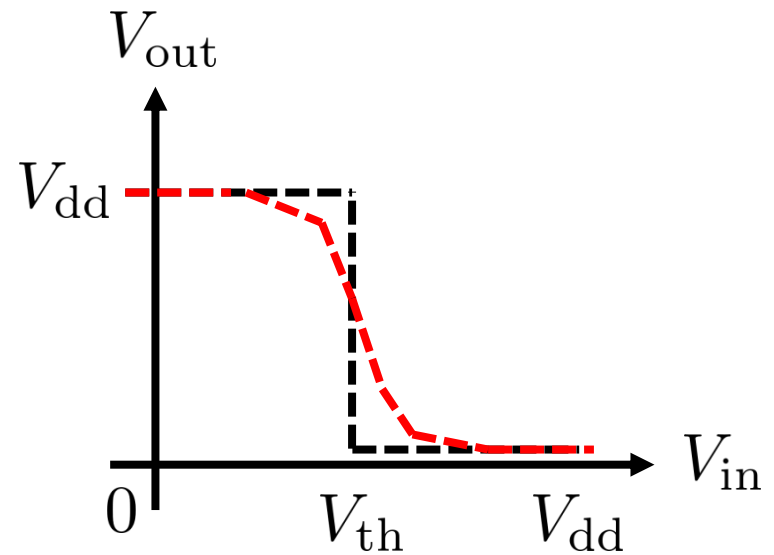
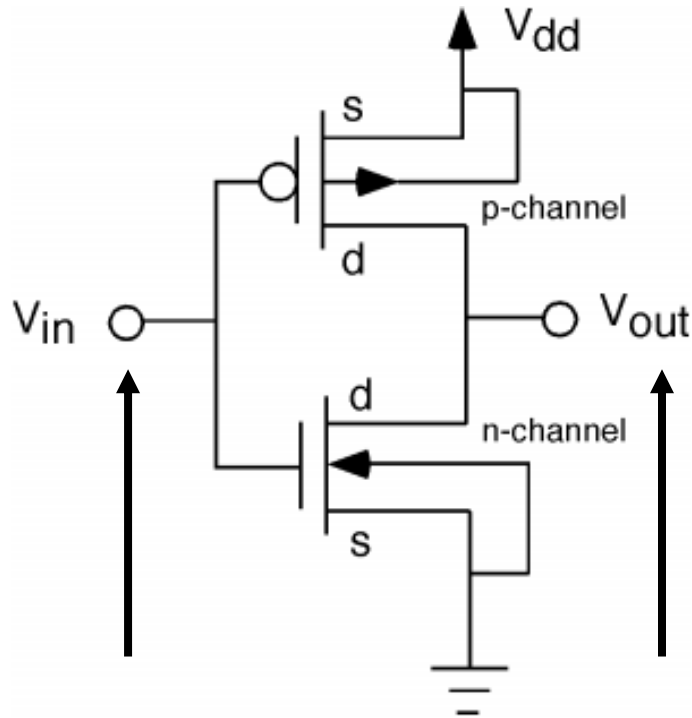
-> used for pull-up

# CMOS Inverter – switch model



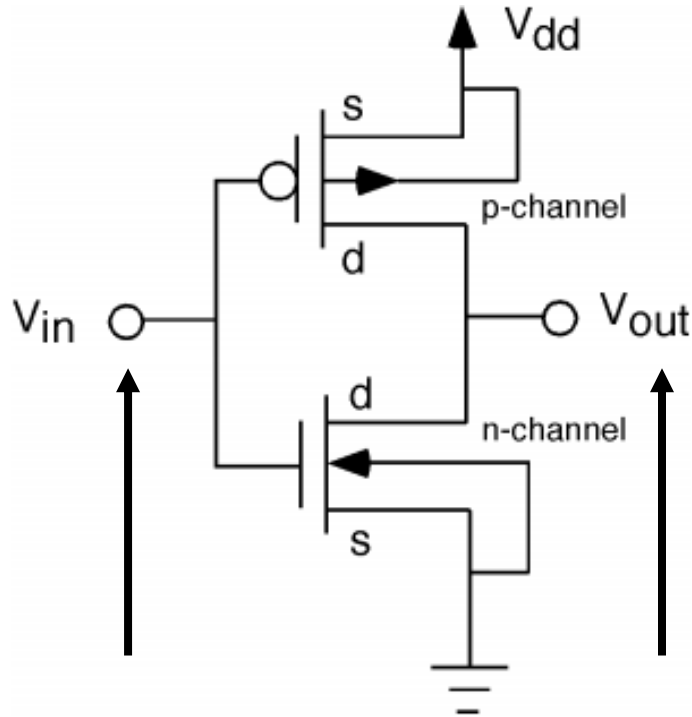
by Bill Wilson, [cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS\\_Logic](https://cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS_Logic)

# CMOS Inverter – detailed static

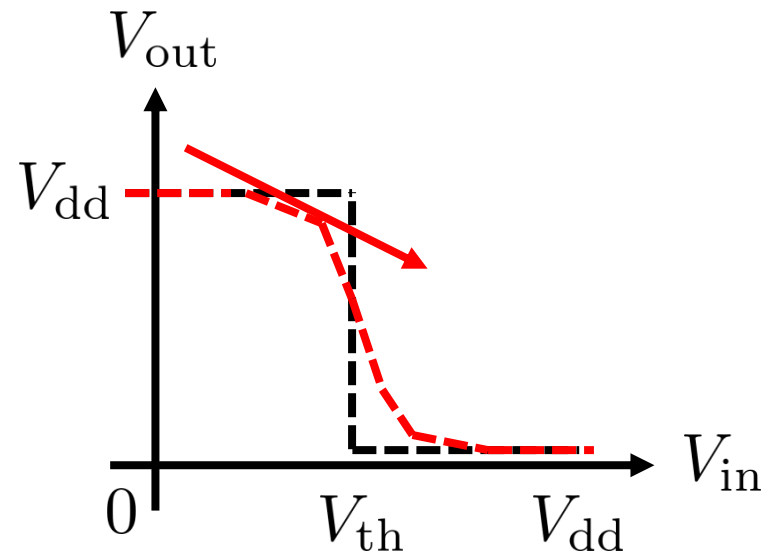


by Bill Wilson, [cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS\\_Logic](https://cnx.org/contents/013d787f-9a59-4567-be18-9c83eac6d884@1/CMOS_Logic)

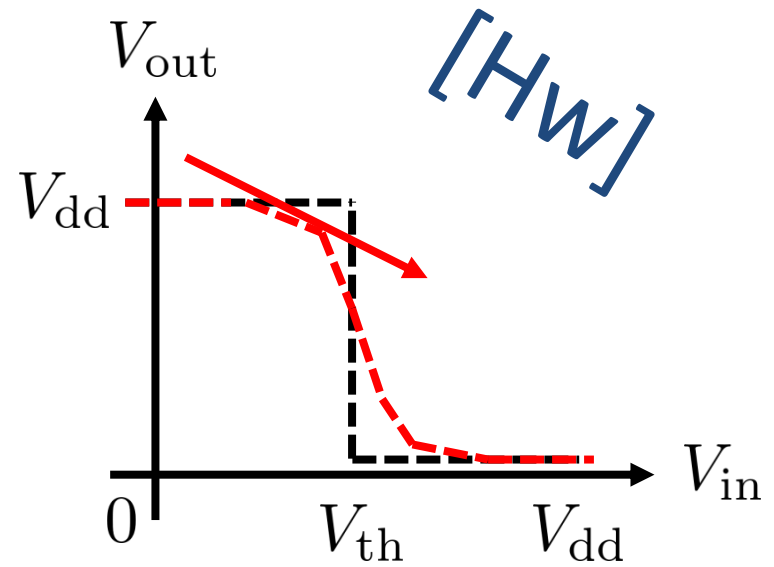
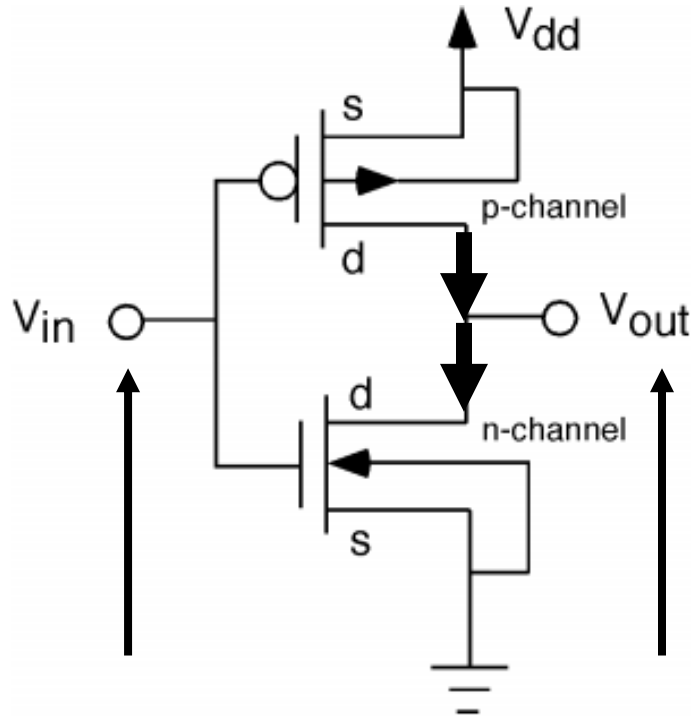
# CMOS Inverter – gain



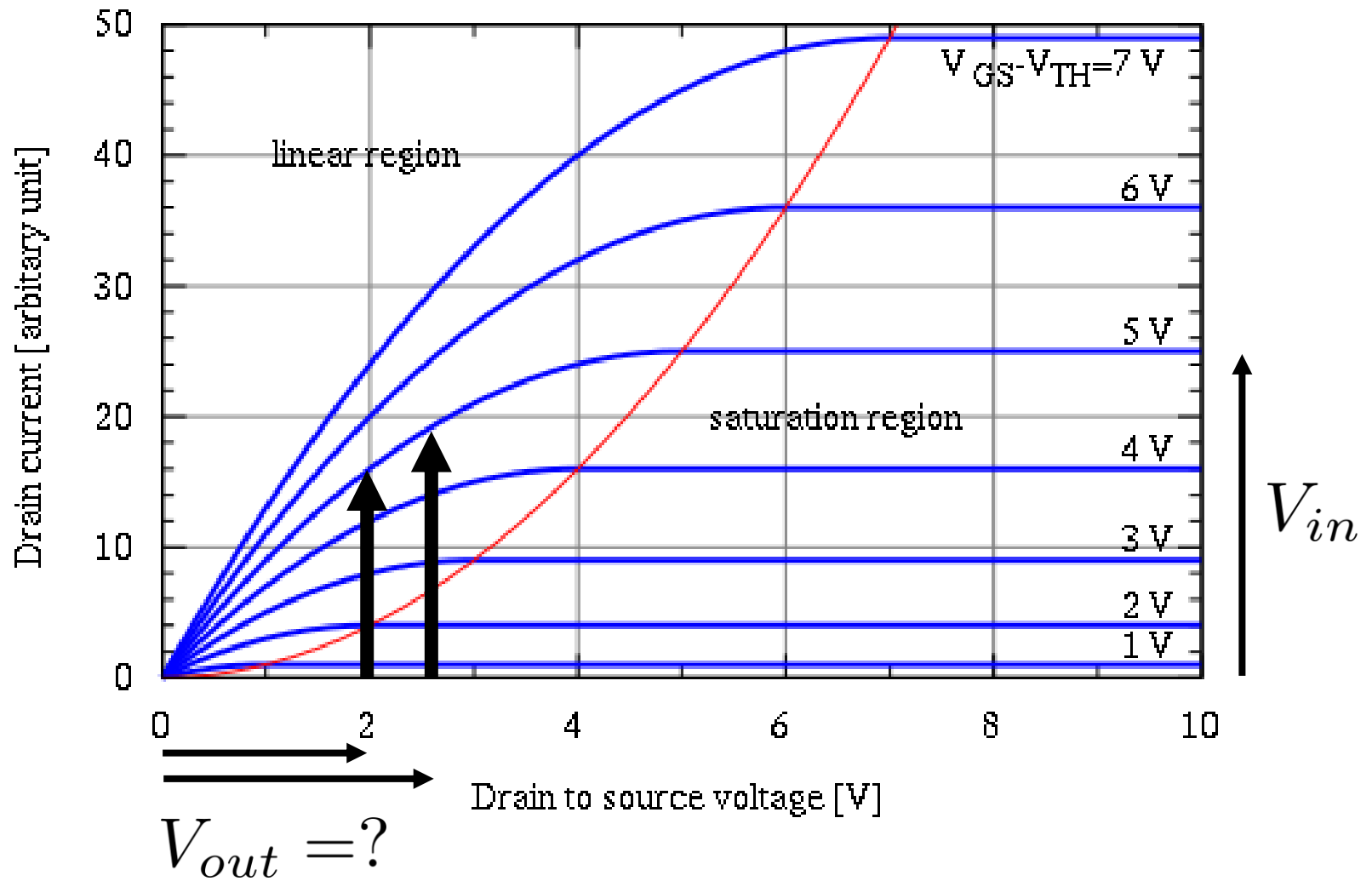
$$g(x) = \left. \frac{dV_{out}}{dV_{in}} \right|_{V_{in}=x}$$



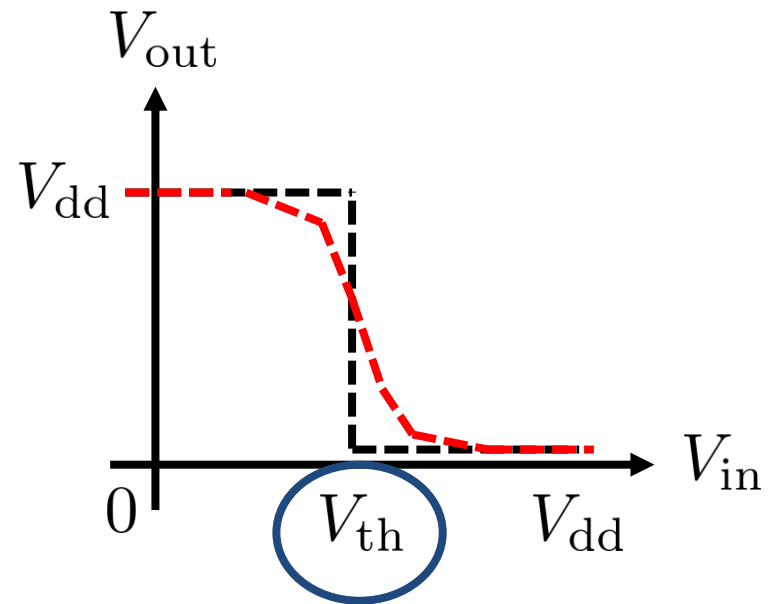
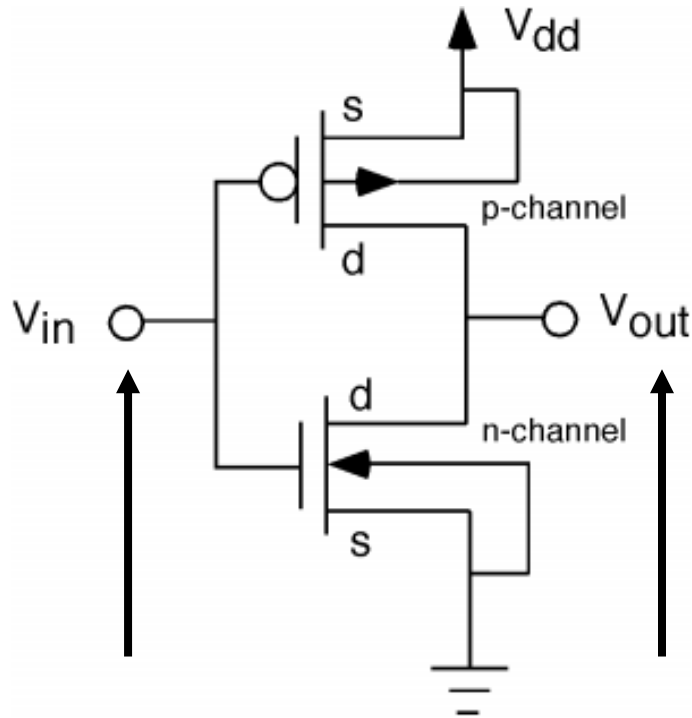
# CMOS Inverter – detailed static







# CMOS Inverter – detailed static



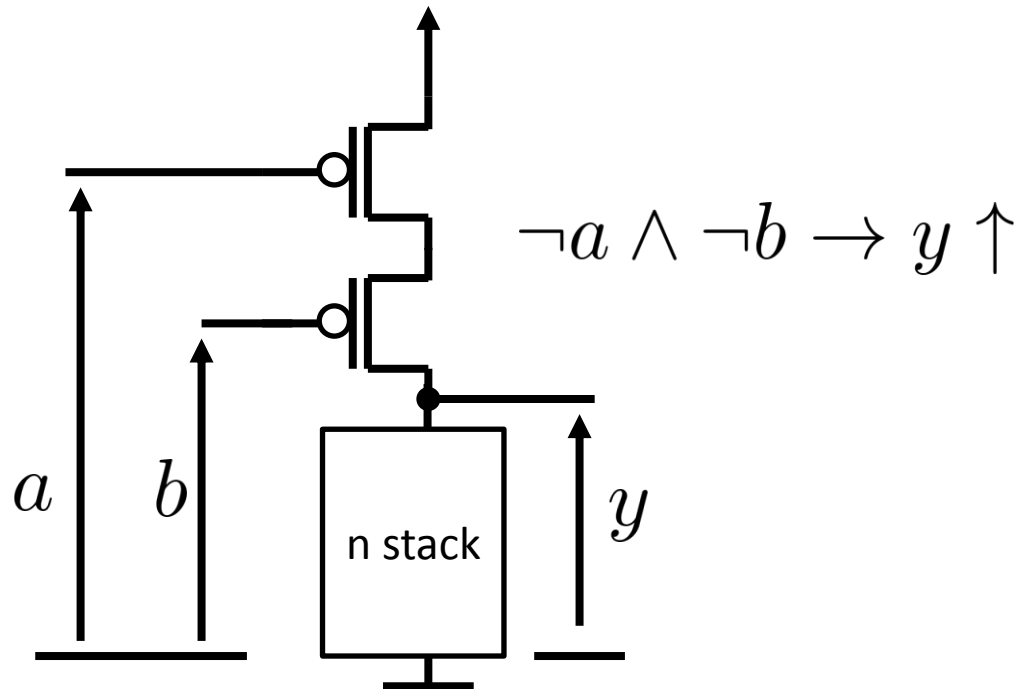
Threshold can be moved by relative sizing  
-> low/high-threshold INV

# CMOS Design

Combinational Logic:

n-stack: down transition  $G \rightarrow y \downarrow$

p-stack: up transition  $\neg G \rightarrow y \uparrow$

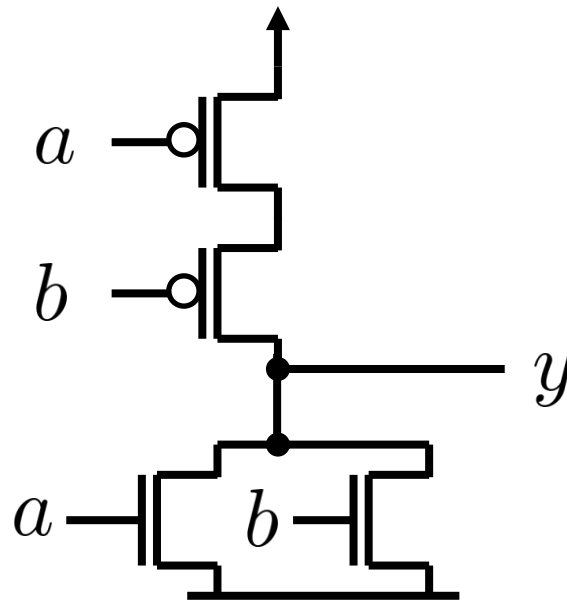


# NOR

Combinational Logic:

n-stack: down transition  $a \vee b \rightarrow y \downarrow$

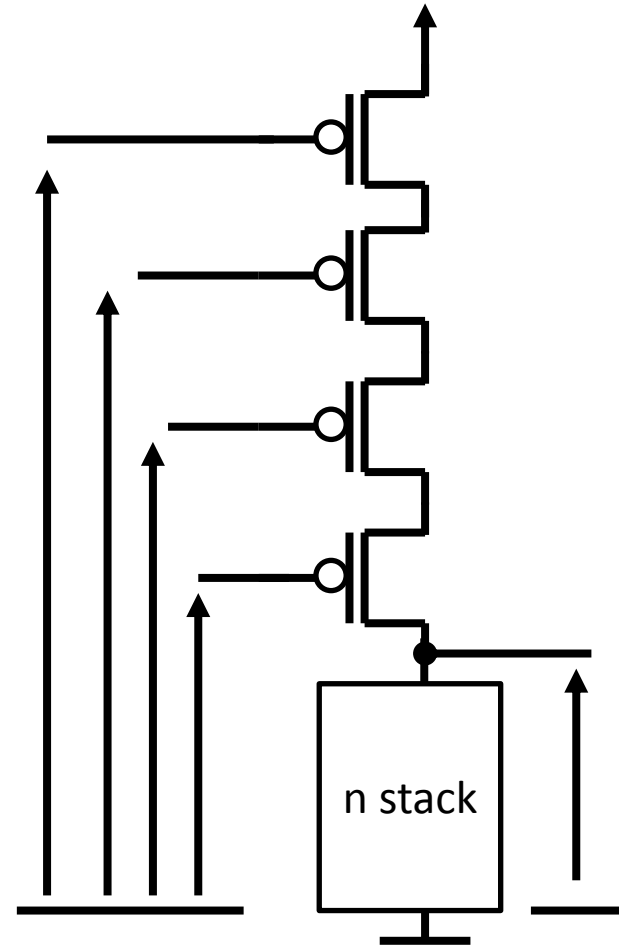
p-stack: up transition  $\neg(a \vee b) \rightarrow y \uparrow$



# CMOS Design

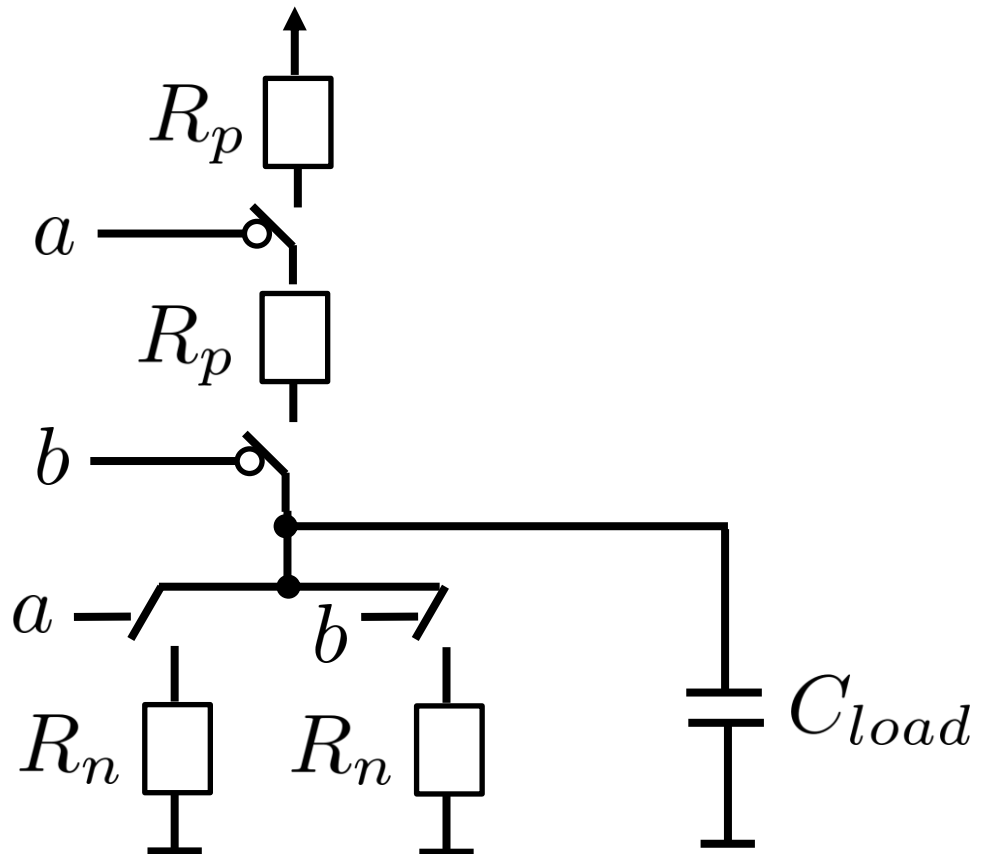
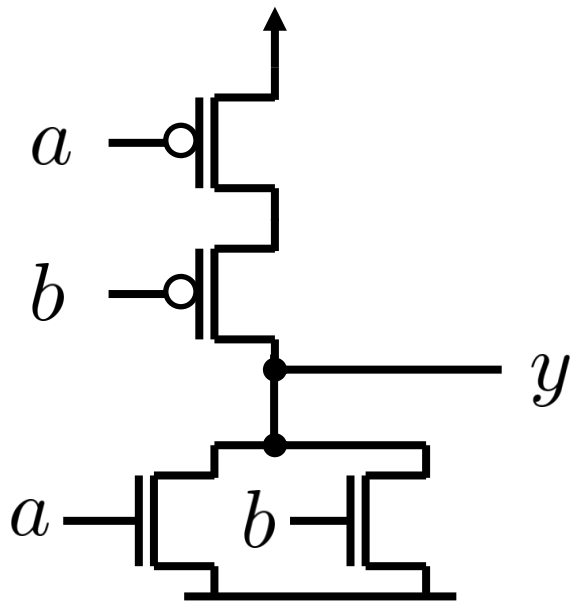
Deep stacks slow!  
esp. mind deep p-stacks

Reason: remember  
resistor/switch model



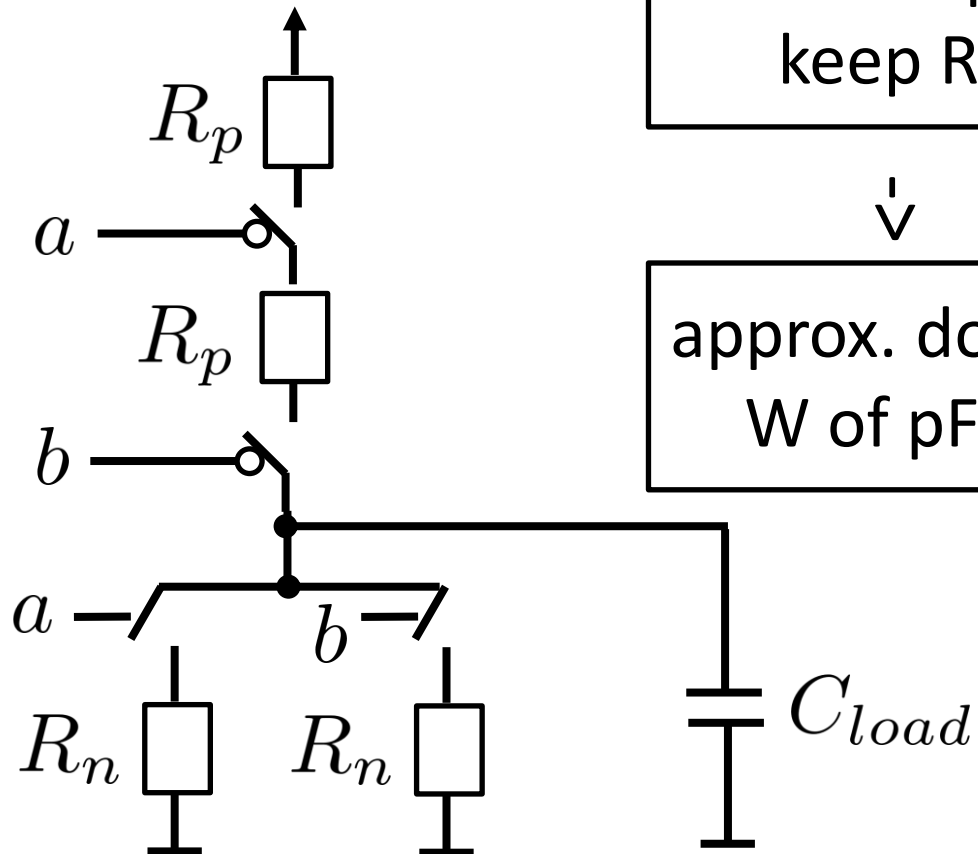
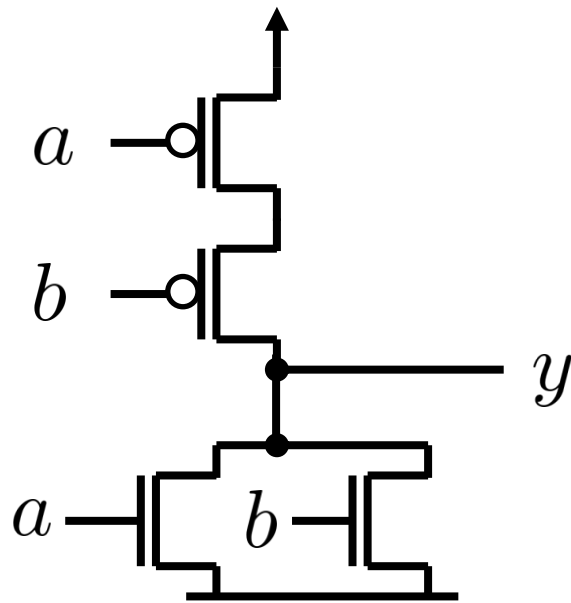
# CMOS Design

We want NOR to be as fast as INV.



# CMOS Design

We want NOR to be as fast as INV ->



half  $R_p$   
keep  $R_n$



approx. double  
W of pFET

# State holding logic?

$$G_{\text{down}} \rightarrow y \downarrow$$

$$G_{\text{up}} \rightarrow y \uparrow$$

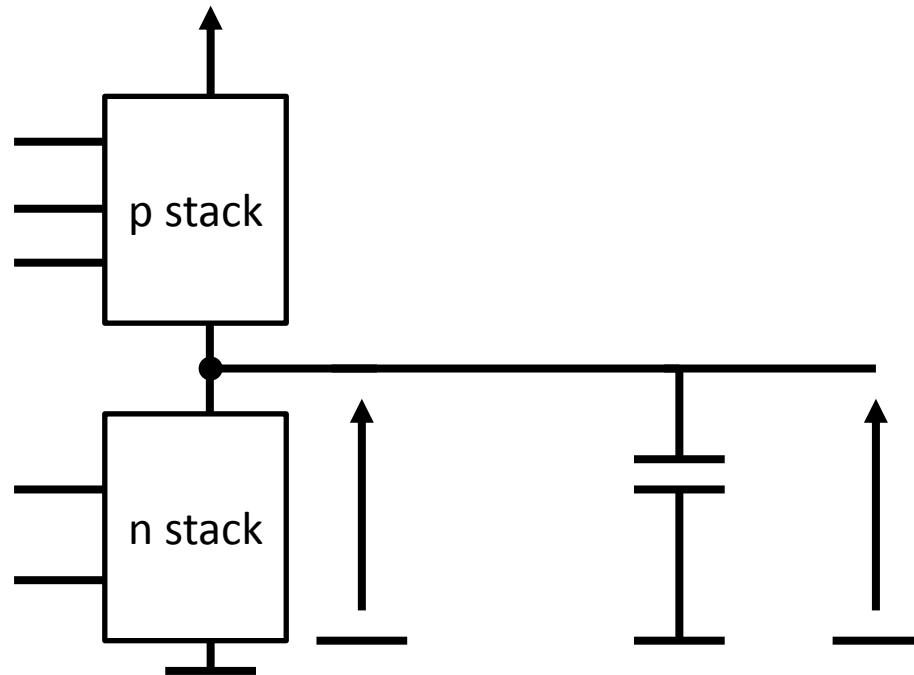
-> statesizer!



# V1 - State holding logic

$$G_{\text{down}} \rightarrow y \downarrow$$

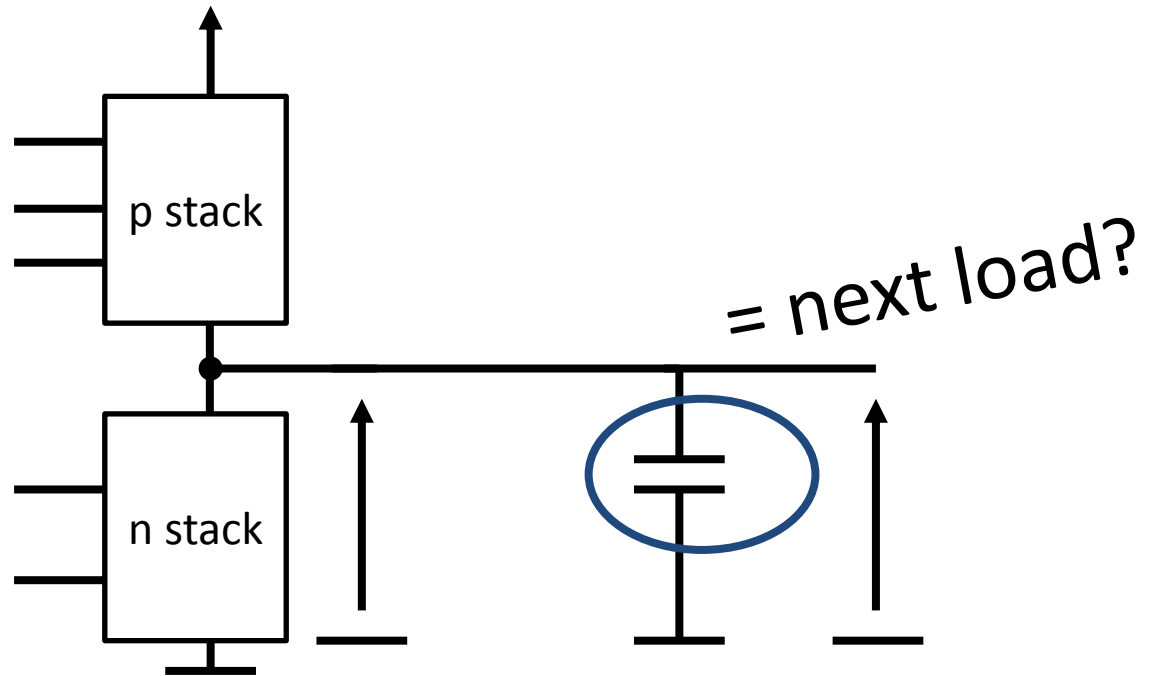
$$G_{\text{up}} \rightarrow y \uparrow$$



# V1' - State holding logic

$$G_{\text{down}} \rightarrow y \downarrow$$

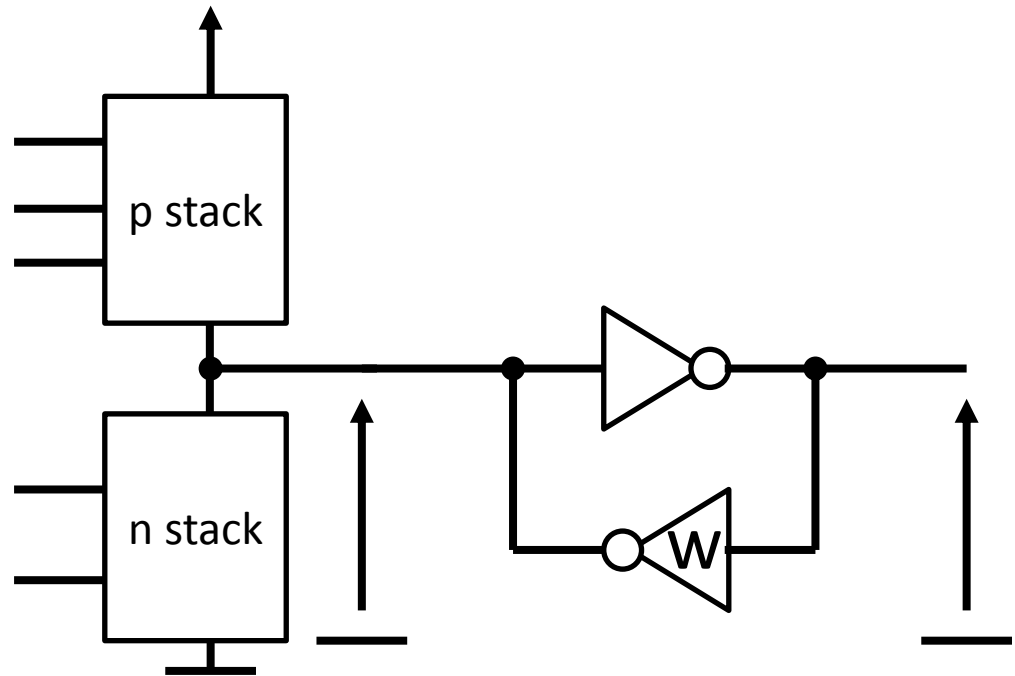
$$G_{\text{up}} \rightarrow y \uparrow$$



# V2 - State holding logic

$$G_{\text{down}} \rightarrow y \downarrow$$

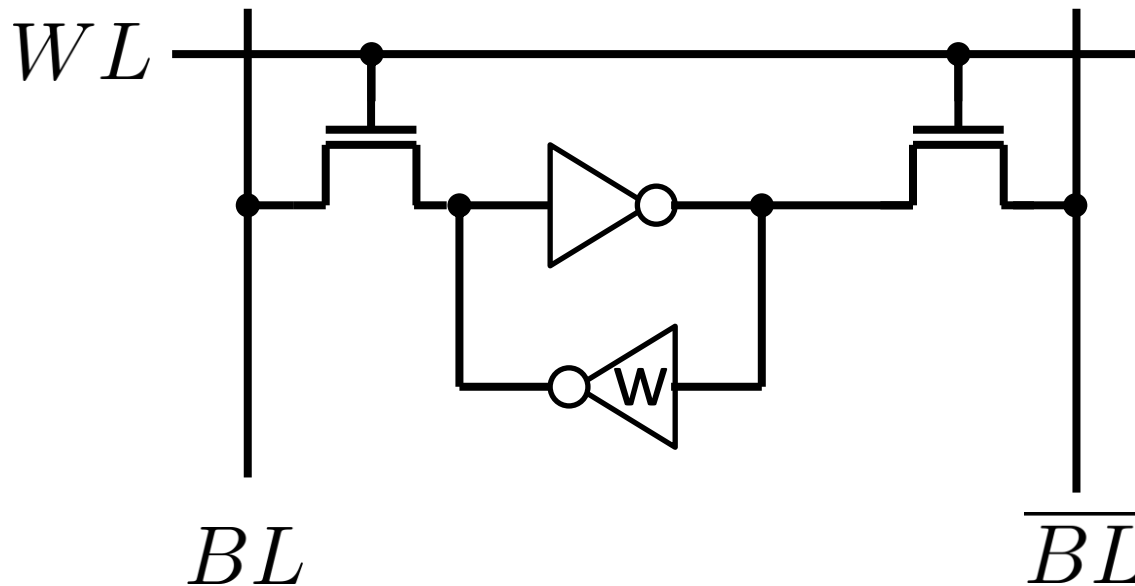
$$G_{\text{up}} \rightarrow y \uparrow$$



# State holding logic

Both used in memory design...

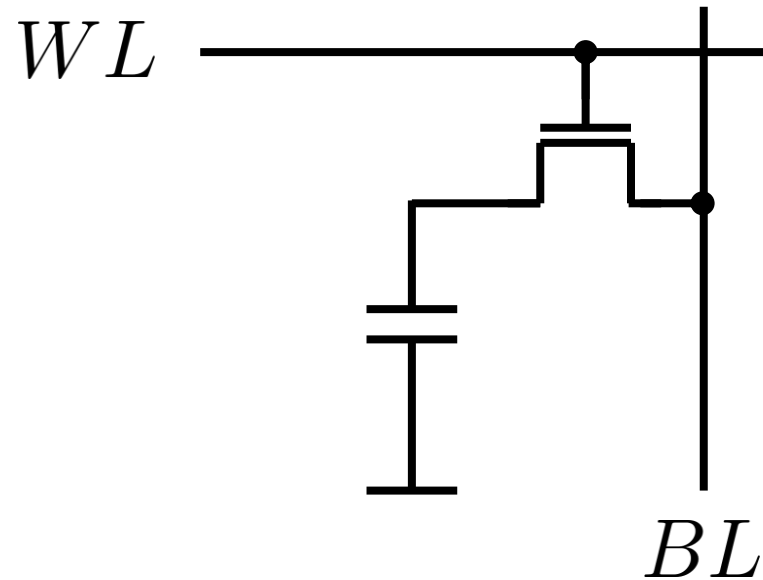
6T-SRAM cell



# State holding logic

Both used in memory design...

DRAM cell (refresh  $\sim 20\text{Hz}$ )



# V3 - State holding logic

[Hw]

$$\begin{array}{l} G_{\text{down}} \rightarrow y \downarrow \\ G_{\text{up}} \rightarrow y \uparrow \end{array} \quad \rightarrow \quad \begin{array}{l} G_{\text{down}} \vee (\neg y \wedge \neg G_{\text{up}}) \rightarrow y \downarrow \\ G_{\text{up}} \vee (y \wedge \neg G_{\text{down}}) \rightarrow y \uparrow \end{array}$$

$$\begin{array}{l} \rightarrow \\ \quad G_{\text{down}} \vee (\neg y \wedge \neg G_{\text{up}}) \rightarrow y' \downarrow \\ \quad G_{\text{up}} \vee (y \wedge \neg G_{\text{down}}) \rightarrow y' \uparrow \\ \quad \quad \neg y' \rightarrow y \downarrow \\ \quad \quad y' \rightarrow y \uparrow \end{array}$$